The RF Line NPN Silicon RF Power Transistor

... designed for 12.5 Volt VHF large–signal power amplifier applications required in commercial and industrial equipment operating to VHF frequencies.

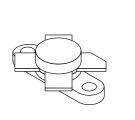
 Specified 12.5 Volt, 175 MHz Characteristics — Output Power = 40 W Power Gain = 4.5 dB Min Efficiency = 70% Min



40 W, 175 MHz RF POWER TRANSISTOR NPN SILICON

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector–Emitter Voltage	VCEO	18	Vdc
Collector-Base Voltage	V _{CBO}	36	Vdc
Emitter-Base Voltage	V _{EBO}	4.0	Vdc
Collector Current — Continuous	IC	7.0	Adc
Total Device Dissipation @ T _C = 25°C (2) Derate above 25°C	PD	80 0.46	Watts W/°C
Storage Temperature Range	T _{stg}	-65 to +200	°C
Stud Torque (1)	_	6.5	in. lb.



CASE 211-07, STYLE 1

ELECTRICAL CHARACTERISTICS (T_C = 25° C unless otherwise noted.)

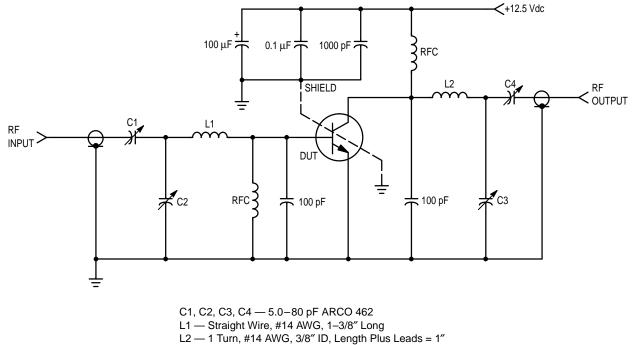
Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS					
Collector–Emitter Breakdown Voltage ($I_C = 100 \text{ mAdc}, I_B = 0$)	V(BR)CEO	18	—	—	Vdc
Collector–Emitter Breakdown Voltage ($I_C = 20 \text{ mAdc}, V_{BE} = 0$)	V(BR)CES	36	—	—	Vdc
Emitter–Base Breakdown Voltage ($I_E = 10 \text{ mAdc}, I_C = 0$)	V(BR)EBO	4.0	—	—	Vdc
Collector Cutoff Current (V _{CE} = 15 Vdc, V _{BE} = 0, T _C = +55°C)	ICES	—	—	10	mAdc
Collector Cutoff Current (V_{CB} = 15 Vdc, I _E = 0)	ICBO	—	—	2.5	mAdc
ON CHARACTERISTICS					
DC Current Gain (I _C = 1.0 Adc, V_{CE} = 5.0 Vdc)	hFE	5.0	—	—	—
DYNAMIC CHARACTERISTICS		•			
Output Capacitance (V _{CB} = 15 Vdc, I _E = 0, f = 0.1 MHz)	C _{ob}	-	170	200	pF
FUNCTIONAL TESTS					
Common–Emitter Amplifier Power Gain (P _{out} = 40 W, V _{CC} = 12.5 Vdc, f = 175 MHz)	GPE	4.5	_	_	dB
Collector Efficiency (P _{out} = 40 W, V _{CC} = 12.5 Vdc, f = 175 MHz)	η	70	—	—	%

NOTES:

1. For repeated assembly use 5 in. lb.

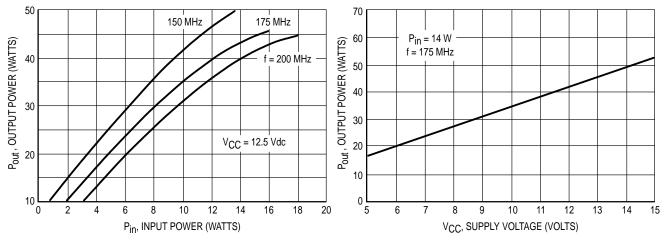
2. These devices are designed for RF operation. The total device dissipation rating applies only when the devices are operated as RF amplifiers.





RFC — VK200–20/4B, FERROXCUBE







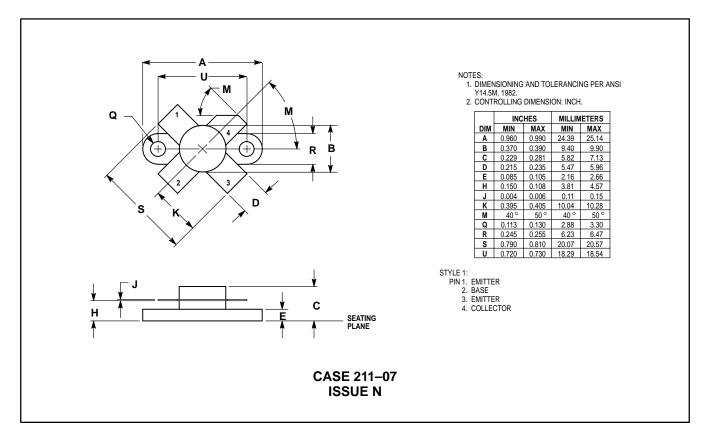


242	WAVEL	ENGTINS	
0 40 - OAD - O	Û.q		50 88m
).81		163	
100 - 100 -		مر مرتق مرتق	100
f = 130 N	/Hz T -!-	門切开	The second
	180 -		SEAL T
f = 130 MHz		日初	99 W.S.
大地理的问题	V _{CC} = 12.5 \	/dc	#15G
大的推进出期	P _{out} = 40 W	- 9457	H
	Frequency	Z _{in}	Z _{OL} *
	MHz	Ohms	Ohms
X: X	130 140	1.00 +1.25 1.00 +1.30	2.88 +0.00 2.88 +0.00
XEALEREE	140	1.00 +1.38	2.88 +0.60
	160	1.00 +1.43	2.85 +1.20
	170 180	1.00 +1.53 1.00 +1.60	2.85 +1.52 2.85 +1.70

 Z_{OL}^* = Conjugate of the optimum load impedance into which the device output operates at a given output power, voltage and frequency.

Figure 4. Series Equivalent Impedance

PACKAGE DIMENSIONS



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